Changmin Lee

List of Publications by Year
in descending order

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Version: 2024-02-01

11 papers	267 citations	1684188 5 h-index	1372567 10 g-index
11 all docs	11 docs citations	11 times ranked	583 citing authors

#	Article	IF	Citations
1	Carrierâ€Type Modulation and Mobility Improvement of Thin MoTe₂. Advanced Materials, 2017, 29, 1606433.	21.0	158
2	Improved Data Retention of InSnZnO Nonvolatile Memory by H₂O₂Treated Al₂O₃Tunneling Layer: A Cost-Effective Method. IEEE Electron Device Letters, 2016, 37, 1272-1275.	3.9	34
3	Pâ€“N Junction Diode Using Plasma Boron-Doped Black Phosphorus for High-Performance Photovoltaic Devices. ACS Nano, 2019, 13, 1683-1693.	14.6	23
4	Characteristics of an Amorphous Carbon Layer as a Diffusion Barrier for an Advanced Copper Interconnect. ACS Applied Materials & Interfaces, 2020, 12, 3104-3113.	8.0	21
5	Homogeneous molybdenum disulfide tunnel diode formed via chemical doping. Applied Physics Letters, 2018, 112, .	3.3	15
6	Effects of H2 High-pressure Annealing on HfO2/Al2O3/In0.53Ga0.47As Capacitors: Chemical Composition and Electrical Characteristics. Scientific Reports, 2017, 7, 9769.	3.3	5
7	Novel Conductive Filament Metalâ€“Interlayerâ€“Semiconductor Contact Structure for Ultralow Contact Resistance Achievement. ACS Applied Materials & Interfaces, 2018, 10, 26378-26386.	8.0	5
8	Electrical properties of HfO2/Al2O3 dielectrics fabricated on In0.53Ga0.47As by using atomic layer deposition at low temperatures (100 - 200 â—¦C). Journal of the Korean Physical Society, 2018, 72, 283-288.	0.7	3
9	Effect of H2S pre-annealing treatment on interfacial and electrical properties of HfO2/Si1â^'xGex (x =) Tj ETQq1 1 0.784314 rgBT /Ove	5.5	2
10	Electrical properties of the HfO₂/Al₂O₃ dielectrics stacked using single- and dual-temperature atomic-layer deposition processes on In_{0.53}Ga_{0.47}As. Semiconductor Science and Technology, 2019, 34, 105018.	2.0	1
11	Shallow doping effect of ZnO treatment using atomic layer deposition process on p-type In_{0.53}Ga_{0.47}As. Journal Physics D: Applied Physics, 2018, 51, 245106.	2.8	0